



CLEAN COPY OF PENDING CLAIMS

Claims 1-2 (Canceled)

Claim 3 (Previously Presented) The fabrication method of a semiconductor device according to claim 8, wherein said step of planarization comprises the step of effecting planarization by polishing said first and second insulation films.

Claim 4 (Previously Presented) The fabrication method of a semiconductor device according to claim 8, wherein said second insulation film includes a silicon oxide film formed by plasma CVD.

Claim 5 (Previously Presented) A fabrication method of a semiconductor device comprising the steps of:

forming a first insulating film, including at least an organic SOG film, on a substrate,

forming a second insulation film on said first insulation film,

introducing impurities at least to a surface of said first insulation film either before or after forming said second insulation film, and

effecting planarization by polishing at least said second insulation film, wherein said step of introducing impurities comprises the steps of

forming a photoresist on a surface of a device before impurities are introduced to said first insulation film, and
introducing impurities into said first insulation film via said photoresist film.

Claim 6 (Previously Presented) A fabrication method of a semiconductor device comprising the steps of:

forming a first insulation film on a substrate,
forming a second insulation film on said first insulation film,
introducing impurities at least to a surface of said first insulation film either before or after forming said second insulation film,
effecting planarization by polishing at least said second insulation film, and
forming a third insulation film on a surface of a device after said first polishing.

Claim 7 (Previously Presented) The fabrication method of a semiconductor device according to claim 8, further comprising the step of:

forming a third insulation film on a surface of a device before said first insulation film is formed.

Claim 8 (Previously Presented) A fabrication method of a semiconductor device comprising the steps of:

forming a first insulating film, including at least an organic SOG film, on a substrate,
forming a second insulation film on said first insulation film,

introducing impurities at least to a surface of said first insulation film either before or after forming said second insulation film, and
effecting planarization by polishing at least said second insulation film.

Claim 9 (Previously Presented) The fabrication method of a semiconductor device according to claim 8, wherein said first insulation film includes a material having a contact angle of purified water of not more than 30° with respect to said first insulation film.

Claim 10 (Canceled)

Claim 11 (Previously Presented) The fabrication method of a semiconductor device according to claim 8, wherein said polishing is carried out by chemical mechanical polishing.

Claim 12 (Original) The fabrication method of a semiconductor device according to claim 11, wherein a surfactant is used in said polishing step.

Claim 13 (Previously Presented) The fabrication method of a semiconductor device according to claim 8, wherein said step of introducing impurities comprises the step of introducing impurities into said first insulation film by implantation.

Claim 14 (Original) The fabrication method of a semiconductor device according to claim 13, wherein said impurities include at least one element selected from the group consisting of argon, boron, nitrogen and phosphorus.

Claim 15 (Canceled)

Claim 16 (Previously Presented) The fabrication method of a semiconductor device according to claim 7, wherein said step of introducing impurities comprises the step of introducing impurities only to a surface of said first insulation film.

Claim 17 (Previously Presented) A fabrication method of a semiconductor device comprising the steps of:

forming a first insulation film on a substrate,
introducing impurities at least to a surface of said first insulation film,
effecting planarization by polishing said first insulation film, and
forming a second insulation film on a surface of a device after said polishing.

Claim 18 (Canceled)

Claim 19 (Previously Presented) A fabrication method of a semiconductor device comprising the steps of:

forming a first insulating film, including at least an organic SOG film, on a substrate,
introducing impurities at least to a surface of said first insulation film,
effecting planarization by polishing said first insulation film, and
forming a second insulation film on a surface of a device before said first insulation film is formed.

Claim 20 (Previously Presented) The fabrication method of a semiconductor device according to claim 7, wherein said first insulation film includes a material having a contact angle of purified water of not more than 30° with respect to said first insulation film.

Claim 21 (Canceled)

Claim 22 (Previously Presented) The fabrication method of a semiconductor device according to claim 7, wherein said polishing is carried out by chemical mechanical polishing.

Claim 23 (Previously Presented) The fabrication method of a semiconductor device according to claim 7, wherein a surfactant is used in said polishing step.

Claim 24 (Previously Presented) The fabrication method of a semiconductor device according to claim 7, wherein said step of introducing impurities comprises the step of introducing impurities into said first insulation film by implantation.

Claim 25 (Previously Presented) The fabrication method of a semiconductor device according to claim 7, wherein said impurities include at least one element selected from the group consisting of argon, boron, nitrogen and phosphorus.

Claim 26 (Previously Presented) A fabrication method of a semiconductor device comprising the steps of:

forming a first insulation film, including at least an organic SOG film, on a substrate,
forming a second insulation film on said first insulation film,
effecting planarization by polishing at least said second insulation film by chemical mechanical polishing using an abrasive liquid including a surfactant, and
introducing impurities into said first insulation after said polishing step.

Claim 27 (Original) The fabrication method of a semiconductor device according to claim 26, wherein said surfactant includes a fatty acid compound.

Claim 28 (Canceled)

Claim 29 (Canceled)

Claim 30 (Canceled)

Claim 31 (Previously Presented) A fabrication method of a semiconductor device, comprising the steps of:

forming a first insulation film including at least an SOG film on a substrate,
forming a second insulation film on said first insulation film,
introducing impurities at least to a surface of said first insulation film either before or after forming said second insulation film,
effecting planarization by polishing at least said second insulation film, and
forming a third insulation film on a surface of a device before said first insulation film is formed.

Claim 32 (Canceled)